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501082.13 (98-0616.12)APPLICATION NO.
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INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)
Vishnu K. AgarwalFILING DATE
August 31, 2000GROUP ART UNIT
2815

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,232,871	08/03/93	Ho	437	190	
	AB 5,552,339	09/03/96	Hsieh	437	190	
	AC 5,733,816	03/31/98	Iyer et al.	438	592	
	AD 6,136,690	10/24/00	Li	438	627	
	AE 6,153,519	11/28/00	Jain et al.	438	681	
	AF 6,245,662	06/12/01	Naik et al.	438	622	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
	AG 355011329 A	01/26/80	JP (Abstract only)			X
	AH 410070091 A	03/10/98	JP (Abstract only)			X

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AI	Anonymous, "Oxide-Free Dielectric/GaAs Interface With No Excess As", IBM Technical Disclosure Bulletin, Vol. 33, No. 11, April 1, 1991, p. 352.
	AJ	Schulz, S.E. et al., "Influence of Water Preclean Before Selective Tungsten CVD on Surface Properties of Interconnect and Intermetal Dielectric Materials", Physica Status Solidi A, Vol. 145, No. 2, October 16, 1994, pp. 311-318.

EXAMINER

DATE CONSIDERED

2/28/02

* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).